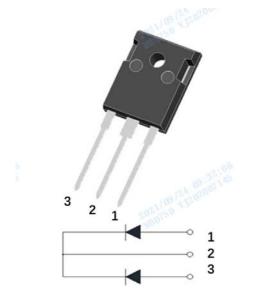


YJD112030NCTG1

Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _F (135°C)	54A ⁽²⁾
Qc	175.6nC ⁽²⁾



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-247AB
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE	
Device marking code			D112030NCTG1	
Reverse voltage (repetitive peak) @ Tj=25°C	V _{RRM}	V	1200	
Reverse voltage (Surge Peak) @ Tj=25°C	V _{RSM}	V	1200	
Reverse voltage (DC) @ Tj=25°C	V _{DC}	V	1200	
Continuous forward current @ T _c =25°C (Per leg/Device)			54/108	
Continuous forward current @ T _c =135°C (Per leg/Device)	I _F	I _F	А	27/54
Continuous forward current @ T _c =160°C (Per leg/Device)			15/30	
Non-repetitive peak forward surge current @ $T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	A	180(1)	
Power Dissipation@ T _c =25° (Per leg/Device)	_	10/	319/625	
Power Dissipation@ T _c =110°C (Per leg/Device)	Ρτοτ	W	138/271	
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	162 ⁽¹⁾	
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175	

 $^{(1)}$ Per Leg, $^{(2)}$ Per Device



Electrical Characteristics (Per Leg)

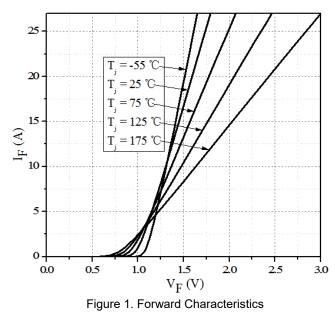
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
Forward valtage drop	V _F V	V	I _F =15A, T _j =25°C	1.46	1.6		
Forward voltage drop		VF	VF	VF	v	I _F =15A, T _j =175°C	2.23
Pavaraa laakaga aurrant		V _R =1200V, T _j =25°C	1	30			
Reverse leakage current	IR	I _R μΑ	V _R =1200V, T _j =175°C	48	-		
Total capacitive charge	Qc	nC	$V_{\text{R}}\text{=}800\text{V},T_{j}\text{=}25^{\circ}\text{C}$, QC= $\int_{0}^{\text{VR}}\text{C}(\text{V})\text{dV}$	89.8			
			V _R =0V, f=1MHZ	1308	-		
Total capacitance	С	pF	V _R =400V, f=1MHZ	86	-		
			V _R =800V, f=1MHZ	62	-		
Capacitance Stored Energy	Ec	μJ	V _R =800V	23.1	-		

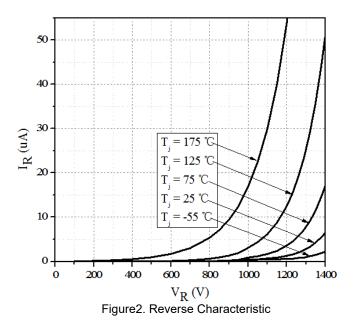
■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C /W	0.24 ⁽²⁾ 0.47 ⁽¹⁾

⁽¹⁾ Per Leg, ⁽²⁾ Per Device

■Typical Characteristics (Per Leg)

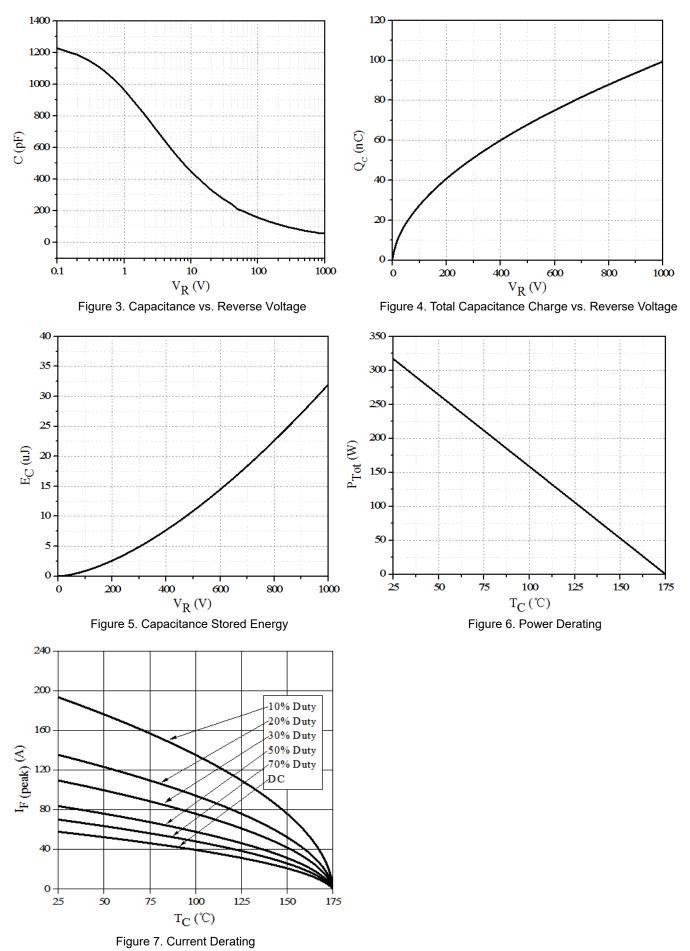




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YJD112030NCTG1





■Typical Characteristics (Device)

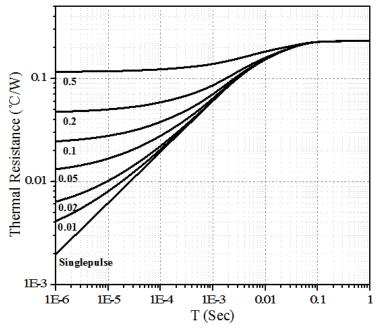
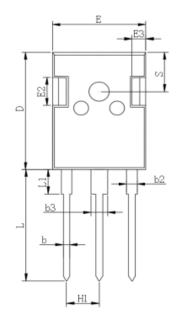
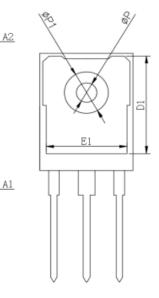


Figure 8. Transient Thermal Impedance



Outline Dimensions





TO-247AB				
Dim	Min	Max		
Α	4.8	5.2		
A1	2.21	2.61		
A2	1.85	2.15		
b	1	1.4		
b2	1.91 A	2.21		
b3	2.8	3.2		
с	0.5	0.7		
D	20.7	21.3		
D1	16.25	16.85		
Е	15.5	16.1		
E1	13	13.6		
E2	4.8	5.2		
E3	2.3	2.7		
L	19.62	20.22		
L1		4.3		
ΦP	3.4	3.8		
ФР1	. 134	7.3		
S	6.15	Тур		
H1	5.44			

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